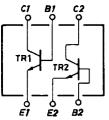


## NPN Epitaxial Planar Silicon Composite Transistor High-Frequency General-Purpose Amp, Differential Amp Applications

#### Features

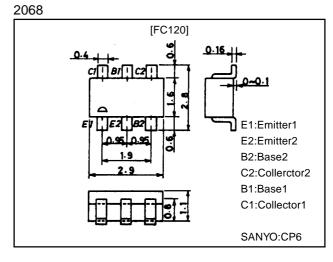
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC120 is formed with two chips, being equivalent to the 2SC3142, placed in one package.
- · Excellent in thermal equilibrium and pair capability.

### **Electrical Connection**



### Package Dimensions

unit:mm



**FC120** 

# Specifications

#### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol         | Conditions | Ratings    | Unit |
|------------------------------|----------------|------------|------------|------|
| Collector-to-Base Voltage    | VCBO           |            | 25         | V    |
| Collector-to-Emitter Voltage | VCEO           |            | 20         | V    |
| Emitter-to-Base Voltage      | VEBO           |            | 3          | V    |
| Collector Current            | Ι <sub>C</sub> |            | 30         | mA   |
| Collector Dissipation        | PC             | 1 unit     | 200        | mW   |
| Total Power Dissipation      | PT             |            | 300        | mW   |
| Junction Temperature         | Tj             |            | 150        | °C   |
| Storage Temperature          | Tstg           |            | -55 to+150 | °C   |

#### **Electrical Characteristics at Ta = 25°C**

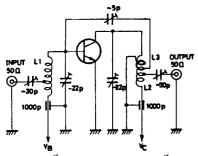
| Parameter                       | Symbol                            | Conditions  | Ratings |      |     | Unit |
|---------------------------------|-----------------------------------|---|---------|------|-----|------|
| Falanielei                      |                                   |   | min     | typ  | max | Unit |
| Collector Cutoff Current        | ICBO                              | V <sub>CB</sub> =10V, I <sub>E</sub> =0             |         |      | 0.1 | μΑ   |
| Emitter Cutoff Current          | IEBO                              | V <sub>EB</sub> =3V, I <sub>C</sub> =0              |         |      | 0.1 | μΑ   |
| DC Current Gain                 | hFE                               | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA            | 80      |      | 200 |      |
| DC Current Gain Ratio           | h <sub>FE</sub> (small/<br>large) | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA            | 0.8     | 0.98 |     |      |
| Base to Emitter Voltage Drop    | V <sub>BE</sub> (large<br>-small) | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA            |         | 1.0  | 15  | mV   |
| Gain-Bandwidth Product          | fT                                | V <sub>CE</sub> =6V, I <sub>C</sub> =4mA            | 450     | 750  |     | MHz  |
| Reverse Transfer Capacitance    | Cre                               | V <sub>CE</sub> =6V, f=1MHz                         |         | 0.6  | 0.9 | pF   |
| Base to Collector Time Constant | r <sub>bb</sub> 'c <sub>c</sub>   | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=31.9MHz |         |      | 19  | ps   |
| Noise Figure                    | NF                                | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=100MHz  |         | 2.2  |     | dB   |
| Power Gain                      | PG                                | V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=100MHz  |         | 28   |     | dB   |

Note: The specifications shown above are for each individual transistor.

Marking:120

SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

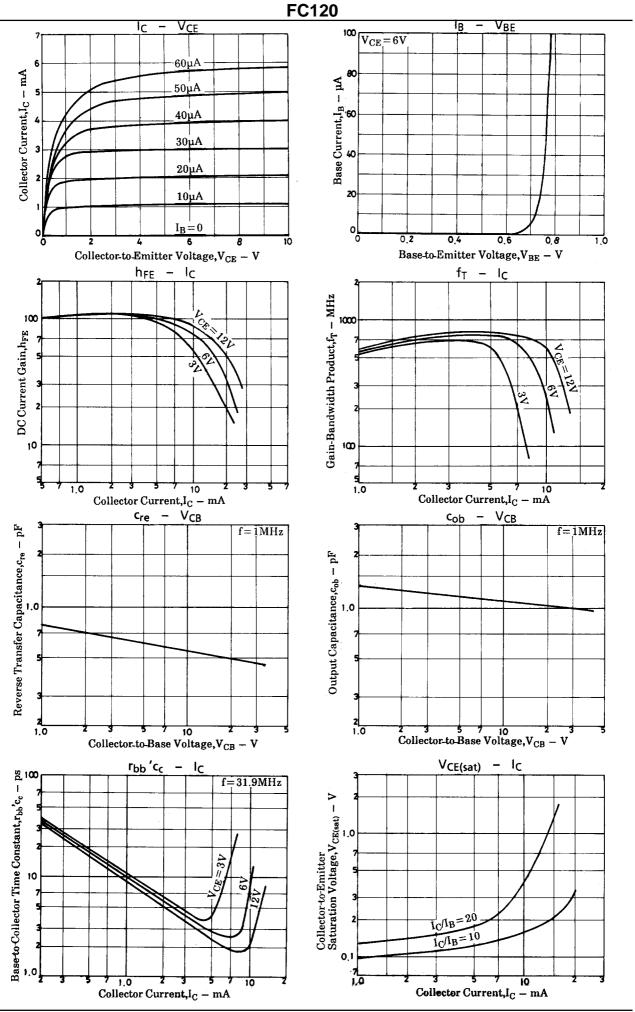


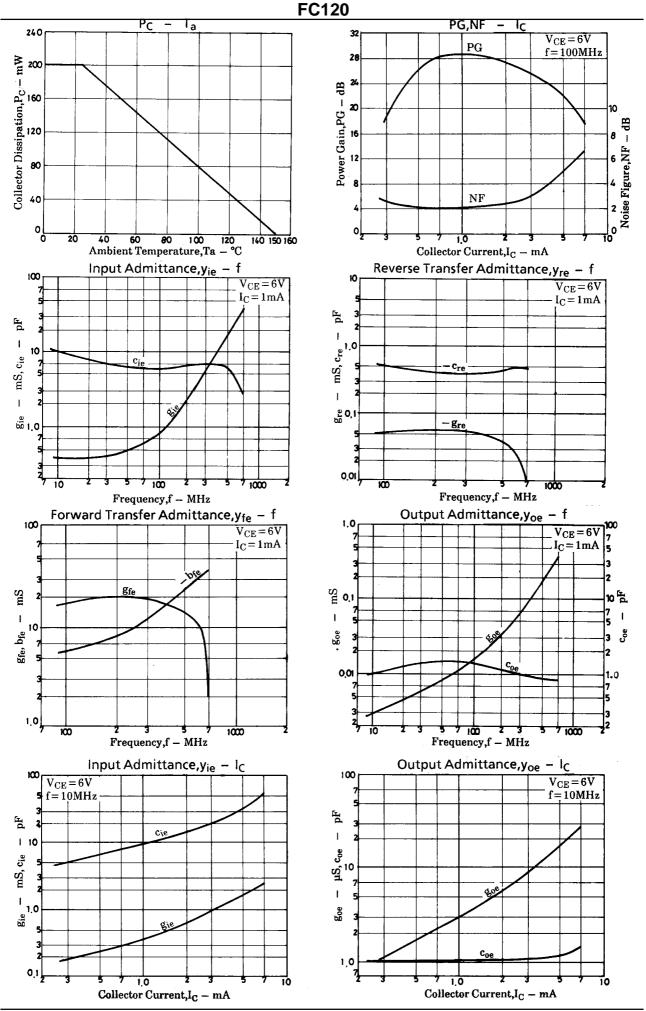


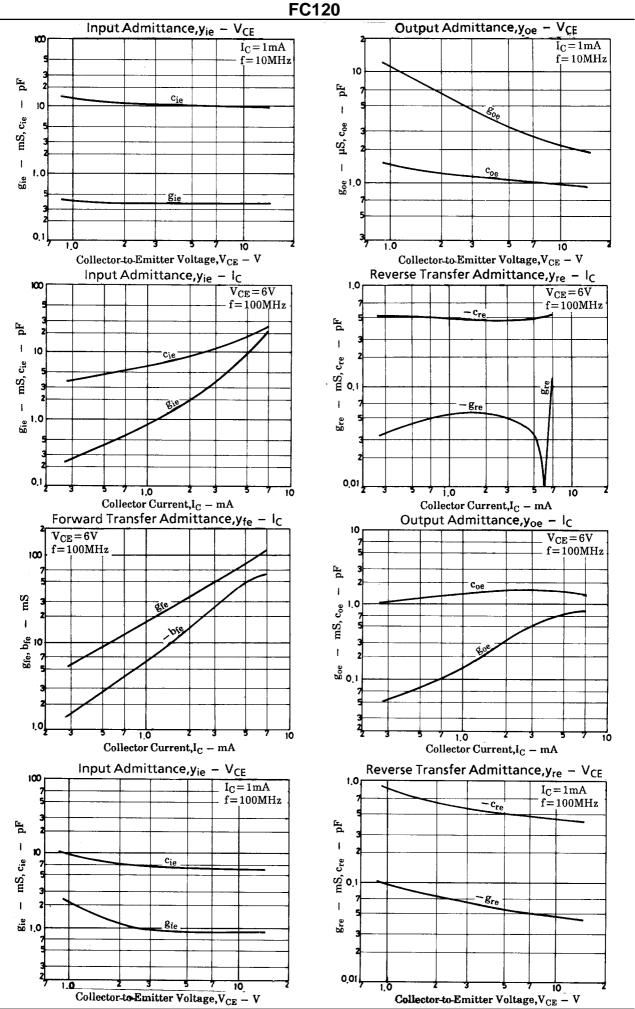
L<sub>1</sub>:1mm<sup>Ø</sup> plated wire, 10mm<sup>Ø</sup> 5T, 15mm pitch, tap : 2T from base side L<sub>2</sub>:1mm<sup>Ø</sup> plated wire, 10mm<sup>Ø</sup> 7T, 10mm pitch, tap : 2T from V<sub>C</sub> side

L<sub>3</sub>:1mm<sup>ø</sup> enamel wire, 10mm<sup>ø</sup> 3T, 10mm pitch

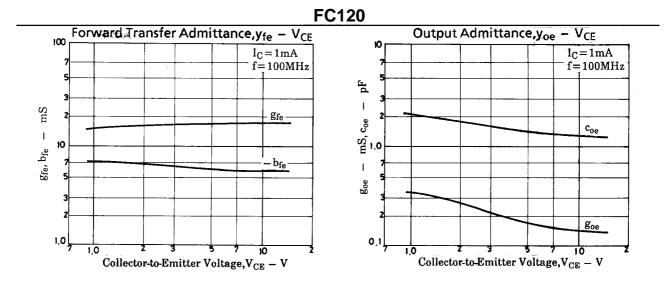
Unit (Capacitance:F)







No.3062-5/6



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